

What is claimed is:

1. A semiconductor integrated circuit, comprising:
a support substrate;
a semiconductor layer that is formed on the entire
5 surface of said support substrate and has a lower
resistivity than the resistivity of said support substrate;
and
first and second circuit sections formed in the
semiconductor layer in an electrically isolated state from
10 each other.
2. The semiconductor integrated circuit according to
Claim 1, wherein the resistivity of said support substrate
is 20 times or more the resistivity of said semiconductor
layer.
- 15 3. The semiconductor integrated circuit according to
Claim 2, wherein the resistivity of said support substrate
is 50 times or more the resistivity of said semiconductor
layer.
4. The semiconductor integrated circuit according to
20 Claim 1, wherein said semiconductor layer is formed on said
support substrate by epitaxial growth.
5. The semiconductor integrated circuit according to
Claim 1, wherein a digital circuit is formed on said first
circuit section, and an analog circuit is formed on said
25 second circuit section.
6. A semiconductor substrate, where a first circuit
section and a second circuit section are formed on the
surface to compose a semiconductor integrated circuit, said

substrate comprising:

a support substrate; and

a semiconductor layer that is formed on the entire surface of the support substrate, has a lower resistivity
5 than the resistivity of said support substrate, and where said first and second circuit sections are electrically isolated from each other and formed in.

7. The semiconductor substrate according to Claim 6, wherein the resistivity of said support substrate is 20
10 times or more the resistivity of said semiconductor layer.

8. The semiconductor substrate according to Claim 7, wherein the resistivity of said support substrate is 50 times or more the resistivity of said semiconductor layer.

9. The semiconductor substrate according to Claim 6,
15 wherein said semiconductor layer is formed on said support substrate by epitaxial growth.

10. The semiconductor substrate according to Claim 6, wherein a digital circuit is formed on said first circuit section, and an analog circuit is formed on said second
20 circuit section.